



TET ESTEL AS
ESTONIA

**June
2013**

**Series
D253-2000**

**Rectifier Press-Pack
Diode
Type D253-2000**

Designed for rectifiers and industrial applications

Maximum mean forward current	I_{FAV} 2000 A						
Maximum repetitive peak reverse voltage	U_{RRM} 1400 ÷ 2400 V						
Reverse recovery time	trr (typ) 40 µs						
U _{RRM} , V	1400	1500	1600	1800	2000	2200	2400
Voltage code	14	15	16	18	20	22	24
Tvj, °C	- 60 ÷ 175						

MAXIMUM ALLOWABLE RATINGS

Symbols and parameters		Units	D253-2000	Conditions	
I _{FAV}	Mean forward current	A	2000 2390 3310	Tc=115 °C, Tc=100 °C, Tc=55 °C, 180° half-sine wave, 50 Hz	
I _{FRMS}	RMS forward current	A	3140	Tc=115 °C	
I _{FSM}	Surge forward current	kA	36 40	Tvj=175°C Tvj=25°C	tp=10 ms
I ² t	Limiting load integral	kA ² s	6480 8000	Tvj=175°C Tvj=25°C	UR=0
U _{RRM}	Repetitive peak reverse voltage	V	1400÷2400	Tj min≤Tvj≤TjM 180° half-sine wave, 50 Hz	
U _{RSR}	Non-repetitive peak reverse voltage	V	1500÷2500	Tj min≤Tvj≤TjM 180° half-sine wave tp=10 ms, Single pulse	
T _{stg}	Storage temperature	°C	-60÷80		
T _{vj}	Junction temperature	°C	-60÷175		

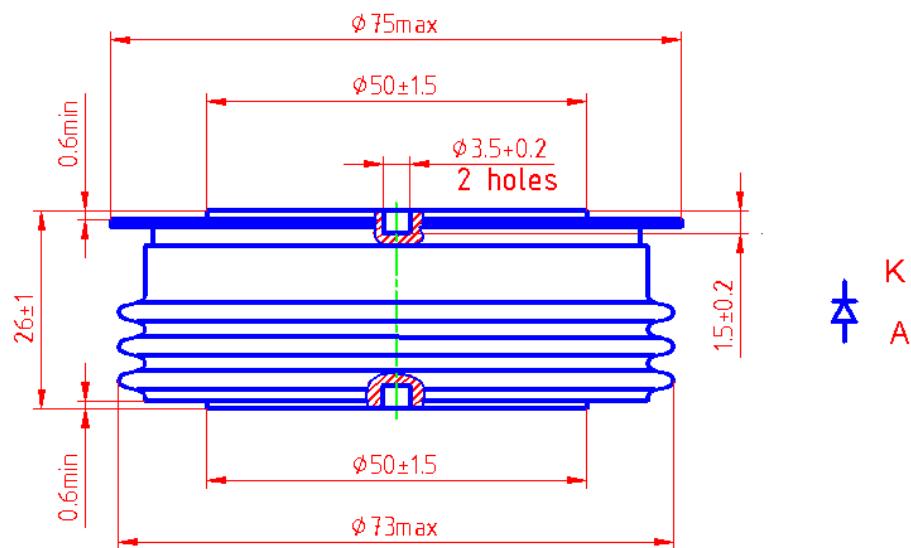
CHARACTERISTICS

U _{FM}	Peak forward voltage	V	1,6	Tvj=25°C, I _{TM} =3,14 I _{FAV}
U _{F(TO)}	Threshold voltage	V	0,93	Tvj=175°C 1,57 I _{FAV} < I _T <4,71 I _{FAV}
R _T	Forward slope resistance	mΩ	0,11	
I _{RRM}	Repetitive peak reverse current	mA	90	Tvj=175°C, UR= U _{RRM}

CHARACTERISTICS				
Symbols and parameters		Units	D253-2000	Conditions
Qrr	Recovered charge (typ)	µC	3600	Tvj=175°C I _F =2000 A dI _R /dt =10 A/µs U _R =100V
trr	Reverse recovery time (typ)	µs	40	
Irrm	Peak reverse recovery current (typ)	A	180	
Rthjc	Thermal resistance junction to case	°C/W	0,02	

ORDERING				
	D	253	2000	22
	1	2	3	4

1. Diode
2. Design version
3. Mean forward current, A
4. Voltage code (22=2200 V)



Mounting force : 19 ÷ 28 kN
Weight : 580 grams